PRODUCT RELIABILITY REPORT

Platform: S150E2.0

--150V E-Mode GaN FET

Reliability Department No. 39 Jin Yuan Er Rd. Hi-Tech District, Zhuhai City, 519085 Guangdong Province P.R. China Tel: 0756-3819888



1. Platform Information

Platform	S150E2.0
Product	INN150LA070A
Package	FCLGA (3.20mm x 2.20mm)
BV Rating(V)	150
Process Technology	GaN on Silicon

2. Reliability Tests

Innoscience's E-mode GaN FET was subjected to a variety of reliability tests under the conditions referenced to typical silicon-based power MOSFET. The test items and results were shown as below:

	Product (INN150LA070A)					
Test Items	Test Condition	Sample Size (Unit x Lot)	#Fail	Result		
MSL3	T=30°C, RH=60%, 3 x reflow, 192hrs	25 x 3	0 Fail	Pass		
HTRB	T=150°C, VD=120V, 1000hrs	77 x 3	0 Fail	Pass		
HTGB	T=150°C, VG=5.5V, 1000hrs	77 x 3	0 Fail	Pass		
HTSL	T=150°C	77 x 3	0 Fail	Pass		
TC	-40 to +125°C, Air, 1000Cys	77 x 3	0 Fail	Pass		
HAST	T=130°C, RH=85%, VD=42V, 96hrs	77 x 3	0 Fail	Pass		
HTOL	QR system: Tj=125°C, Vplatform=120V, Power out=120W, Vout=20V, f=130KHz	8 x 3	0 Fail	Pass		
НВМ	All Pins	3 x 1	0 Fail	Class 1B		
CDM	All Pins	3 x 1	0 Fail	Class C2b		

Moisture Sensitivity Level (MSL3)

Parts were baked at 125°C for 24 hours, and then subjected to 60%RH at 30°C for a stress period of 192 hours. The parts were also subjected to three cycles of Pb-free reflow in accordance with the IPC/JEDEC standard J-STD-020.

Pass criteria: All units must pass the min/max limits of the datasheet.

Test Item	Product Number	Test Condition	Fail #	Sample Size (Unit x Lot)	Duration (Hrs)
MSL3	INN150LA070A	T=30°C, RH=60%, 3 x reflow	0	25 x 3	192



High Temperature Reverse Bias (HTRB)

Parts were subjected to 80% of the rated drain-source voltage at the maximum rated temperature for a stress period of 1000 hours. The testing was done in accordance with the JEDEC Standard JESD22-A108.

Pass criteria: All units must pass the min/max limits of the datasheet.

Test Item	Product Number	Test Condition	Fail #	Sample Size (Unit x Lot)	Duration (Hrs)
HTRB	INN150LA070A	T=150°C, VD=120V, VG=VS=0V	0	77 x 3	1000

High Temperature Gate Bias (HTGB)

Parts were subjected to 5.5V gate-source bias at the maximum rated temperature for a stress period of 1000 hours. The testing was done in accordance with the JEDEC Standard JESD22-A108.

Pass criteria: All units must pass the min/max limits of the datasheet.

Test Item	Product Number	Test Condition	Fail #	Sample Size (Unit x Lot)	Duration (Hrs)
HTGB	INN150LA070A	T=150°C, VG=5.5V, VD=VS=0V	0	77 x 3	1000

High Temperature Storage Life (HTSL)

Parts were subjected to 150°C for a stress period of 1000 hours. The testing was done in accordance with the JEDEC Standard JESD22-A103.

Pass criteria: All units must pass the min/max limits of the datasheet.

Test Item	Product Number	Test Condition	Fail #	Sample Size (Unit x Lot)	Duration (Hrs)
HTSL	INN150LA070A	T=150°C	0	77 x 3	1000



Temperature Cycling (TC)

Parts were subjected to temperature cycling between -40°C and +125°C for a total of 1000 cycles. Heating rate and cooling rate of 15°C/min. Dwell time of 5 minutes were used in accordance with the JEDEC Standard JESD22-A104.

Pass criteria: All units must pass the min/max limits of the datasheet.

Test Item	Product Number	Test Condition	Fail #	Sample Size (Unit x Lot)	Duration (Cys)
TC	INN150LA070A	-40 to +125°C, Air	0	77 x 3	1000

Highly Accelerated Temperature and Humidity Stress Test (HAST)

Parts were subjected to 42V bias at 85%RH and 130°C for a stress period of 96 hours. The testing was done in accordance with the JEDEC Standard JESD22-A110.

Pass criteria: All units must pass the min/max limits of the datasheet.

Test Item	Product Number	Test Condition	Fail #	Sample Size (Unit x Lot)	Duration (Hrs)
HAST	INN150LA070A	T=130°C, RH=85%, VD=42V,	0	77 x 3	96
IIASI	INNISULAU/UA	VG=VS=0V	O	// x 3	30

High Temperature Operating Life (HTOL)

Parts were subjected to AC-to-DC system test adapted QR topology with SR device $V_{platform}$ =120V bias and F_{SW} =130KHz at junction temperature=125°C for a stress period of 1000 hours. The testing was done in accordance with JEP-180.

Pass criteria: All units must pass the min/max limits of the datasheet.

Test Item	Product Number	Test Condition	Fail #	Sample Size (Unit x Lot)	Duration (Hrs)
HTOL	INN150LA070A	QR system: Tj=125°C, Vplatform=120V, Power out=120W, Vout=20V, f=130KHz	0	8 x 3	1000



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Electro-Static discharge (ESD)

Parts were subjected to HBM (ESDA/JEDEC JS-001) and CDM (ESDA/JEDEC JS-002) test to guarantee that the device can with stand electrostatic voltages during handling.

Pass criteria: All units must pass the min/max limits of the datasheet.

Test Item	Product Number	Test Condition	Passed Voltage	JEDEC Class
НВМ	INN150LA070A	All Pins	(±) 500V	Class 1B
CDM	INN150LA070A	All Pins	(±) 750V	Class C2b

Parts were mounted on to FR4 adaptor cards. Adaptor cards with two copper layers were used. The copper layer thickness was between 1 and 2 oz. SAC305 solder was used to mount the DUTs onto the adaptor cards.

Revision/Updated History

Revision	Reason for Change	Date	Prepared by	Approved by
1.0	Final release	Sen /30/2022	7hizhong Chen	RE: Blanck sun Director

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